### **Complementary Silicon Plastic Power Transistors**

### TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

Designed for use in general purpose amplifier and switching applications.

#### Features

- High Current Gain Bandwidth Product
- Compact TO-220 Package
- These Devices are Pb-Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

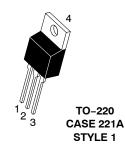
Symbol	Rating	Value	Unit
V <sub>CEO</sub>	Collector – Emitter Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	40 60 80 100	Vdc
V <sub>CB</sub>	Collector–Base Voltage TIP31G, TIP32G TIP31AG, TIP32AG TIP31BG, TIP32BG TIP31CG, TIP32CG	40 60 80 100	Vdc
V <sub>EB</sub>	Emitter-Base Voltage	5.0	Vdc
Ι <sub>C</sub>	Collector Current – Continuous	3.0	Adc
I <sub>CM</sub>	Collector Current – Peak	5.0	Adc
Ι <sub>Β</sub>	Base Current	1.0	Adc
PD	Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	40 0.32	W W/°C
P <sub>D</sub>	Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	2.0 0.016	W W/°C
E	Unclamped Inductive Load Energy (Note 1)	32	mJ
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $I_C = 1.8 \text{ A}, L = 20 \text{ mH}, P.R.F. = 10 \text{ Hz}, V_{CC} = 10 \text{ V}, R_{BF} = 100 \Omega$ 

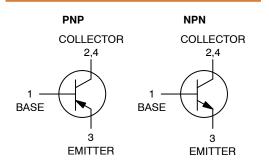
#### THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit		
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W		
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3.125	°C/W		

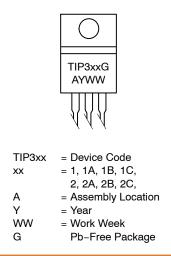
\*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, <u>SOLDERRM/D</u>.



#### 3 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 40–60–80–100 VOLTS, 40 WATTS



#### MARKING DIAGRAM



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

## TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

Symbol	Characteristic	Min	Max	Unit
FF CHARA	CTERISTICS	•		
V <sub>CEO(sus)</sub>		40 60 80 100		Vdc
I <sub>CEO</sub>	Collector Cutoff Current ( $V_{CE} = 30$ Vdc, $I_B = 0$ ) TIP31G, TIP32G, TIP31AG, TIP32AG ( $V_{CE} = 60$ Vdc, $I_B = 0$ ) TIP31BG, TIP31CG, TIP32BG, TIP32CG	-	0.3 0.3	mAdc
I <sub>CES</sub>	Collector Cutoff Current ( $V_{CE} = 40 \text{ Vdc}, V_{EB} = 0$ ) TIP31G, TIP32G ( $V_{CE} = 60 \text{ Vdc}, V_{EB} = 0$ ) TIP31AG, TIP32AG ( $V_{CE} = 80 \text{ Vdc}, V_{EB} = 0$ ) TIP31BG, TIP32BG ( $V_{CE} = 100 \text{ Vdc}, V_{EB} = 0$ ) TIP31CG, TIP32CG		200 200 200 200	μAdc
I <sub>EBO</sub>	Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}, I_C = 0$ )	_	1.0	mAdc
N CHARAC	TERISTICS (Note 2)	-		
h <sub>FE</sub>	DC Current Gain ( $I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$ ) ( $I_C = 3.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$ )	25 10	- 50	-
V <sub>CE(sat)</sub>	Collector–Emitter Saturation Voltage $(I_C = 3.0 \text{ Adc}, I_B = 375 \text{ mAdc})$	_	1.2	Vdc
V <sub>BE(on)</sub>	Base-Emitter On Voltage (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	-	1.8	Vdc
YNAMIC CH	IARACTERISTICS			
f <sub>T</sub>	Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	3.0	_	MHz
h <sub>fe</sub>	Small–Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	20	-	-

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

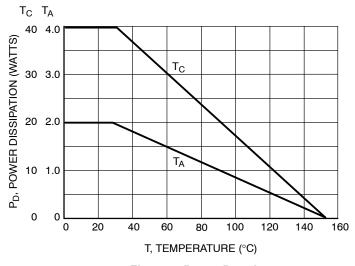
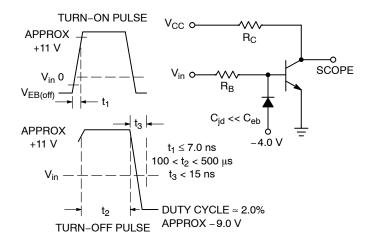
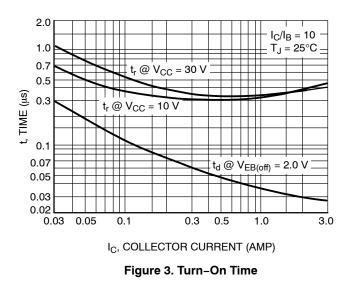


Figure 1. Power Derating



 $\rm R_B$  and  $\rm R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS.





### TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

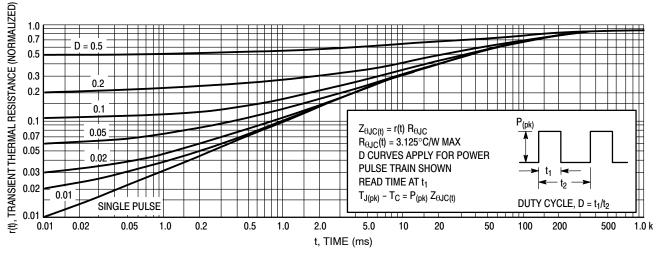


Figure 4. Thermal Response

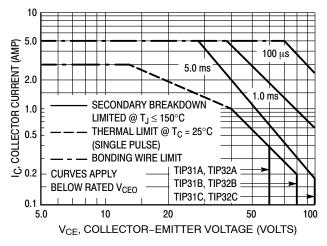
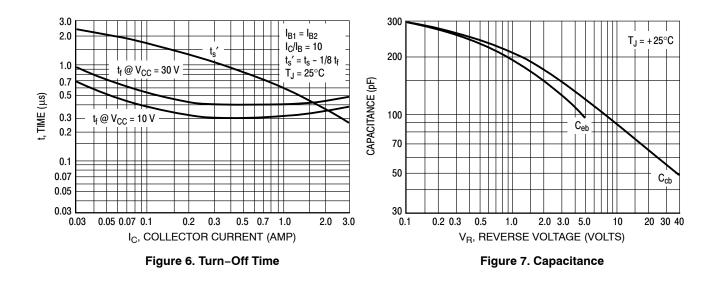


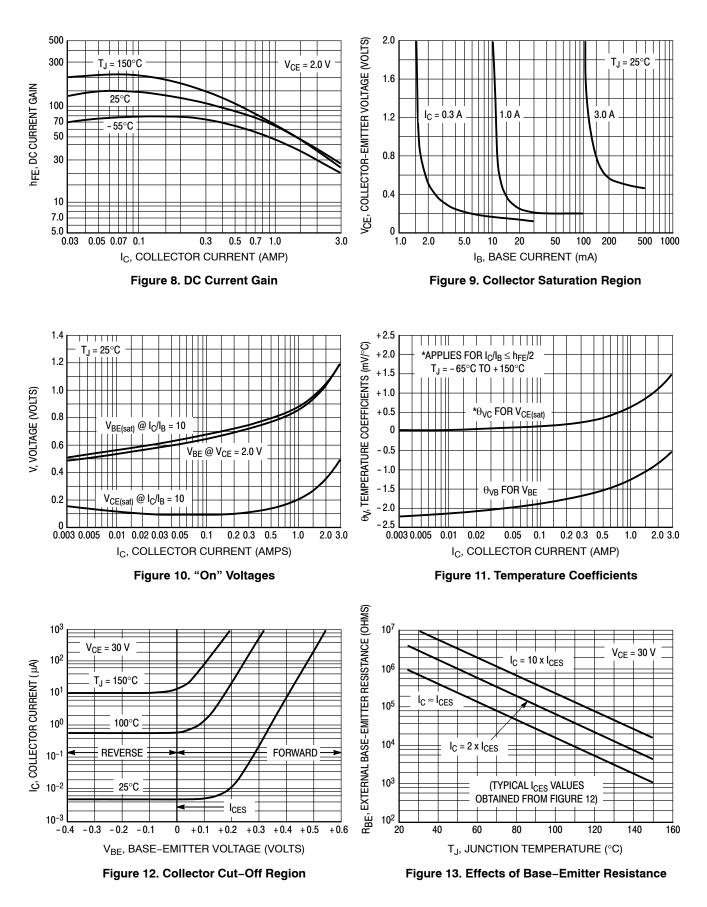
Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}$ C;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}$ C.  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



#### TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)



## TIP31G, TIP31AG, TIP31BG, TIP31CG (NPN), TIP32G, TIP32AG, TIP32BG, TIP32CG (PNP)

#### **ORDERING INFORMATION**

Device	Package	Shipping			
TIP31AG	TO-220 (Pb-Free)	50 Units / Rail			
TIP31BG	TO-220 (Pb-Free)	50 Units / Rail			
TIP31CG	TO-220 (Pb-Free)	50 Units / Rail			
TIP32G	TO-220 (Pb-Free)	50 Units / Rail			
TIP32AG	TO-220 (Pb-Free)	50 Units / Rail			
TIP32BG	TO-220 (Pb-Free)	50 Units / Rail			
TIP32CG	TO-220 (Pb-Free)	50 Units / Rail			

#### **DISCONTINUED** (Note 3)

TIP31G	TO-220	50 Units / Rail
	(Pb-Free)	

3. DISCONTINUED: This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on <u>www.onsemi.com</u>.

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	<b>TO-22</b> CASE 2 ISSUE	21A					DATE	13 JAN 2022
SCALE 1:1		PLANE 1 2 3.	. CONT . DIMEI LEA	ROLLING D NSION Z DE D IRREGUL/ WIDTH FOR	AND TOLERAI IMENSION: IN FINES A ZONI ARITIES ARE A F102 DEVICE	NCHES E WHERE AL ALLOWED. E = 1.35MM	L BODY AND	
A A				INC	1	MILLIM		
	Ŭ		DIM	MIN.	MAX.	MIN.	MAX.	
1 2 3			A	0.570	0.620	14.48	15.75	
			B	0.380	0.415	9.66	10.53	
<u>╄</u> <u></u>			C D	0.160	0.190	4.07	4.83	
			F	0.025	0.038	0.64 3.60	0.96 4.09	
Z-J K			G	0.095	0.101	2.42	2.66	
			н	0.110	0.161	2.42	4.10	
				0.014	0.024	0.36	0.61	
			ĸ	0.500	0.562	12.70	14.27	
∨4	R —		L	0.045	0.060	1.15	1.52	
G	J <del>→    →</del>		N	0.190	0.210	4.83	5.33	
_ <b>→</b>    <del>→</del> D			Q	0.100	0.120	2.54	3.04	
N			R	0.080	0.110	2.04	2.79	
			s	0.045	0.055	1.15	1.41	
			т	0.235	0.255	5.97	6.47	
			U	0.000	0.050	0.00	1.27	
			V	0.045		1.15		
			Z		0.080		2.04	
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